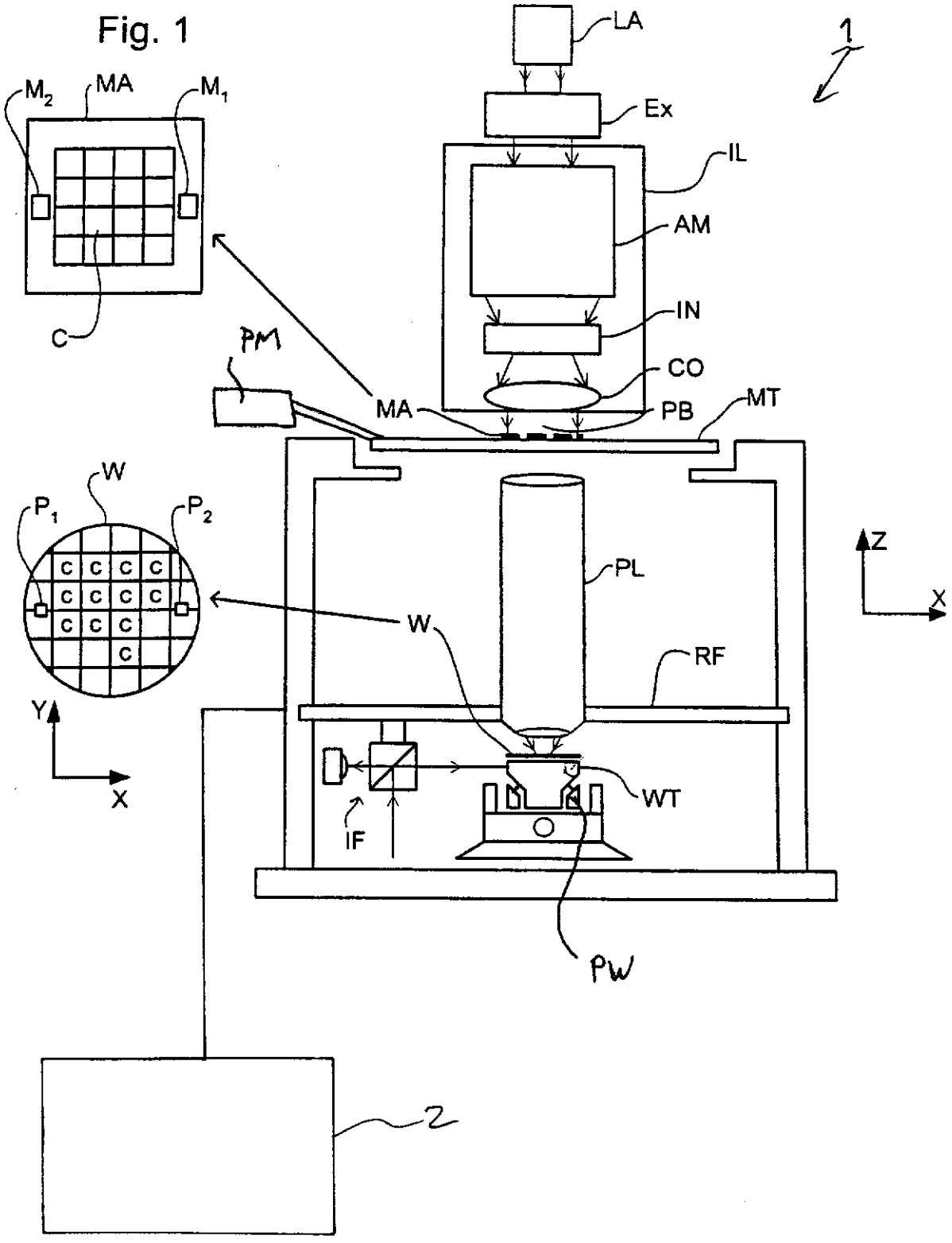
Fig. 1



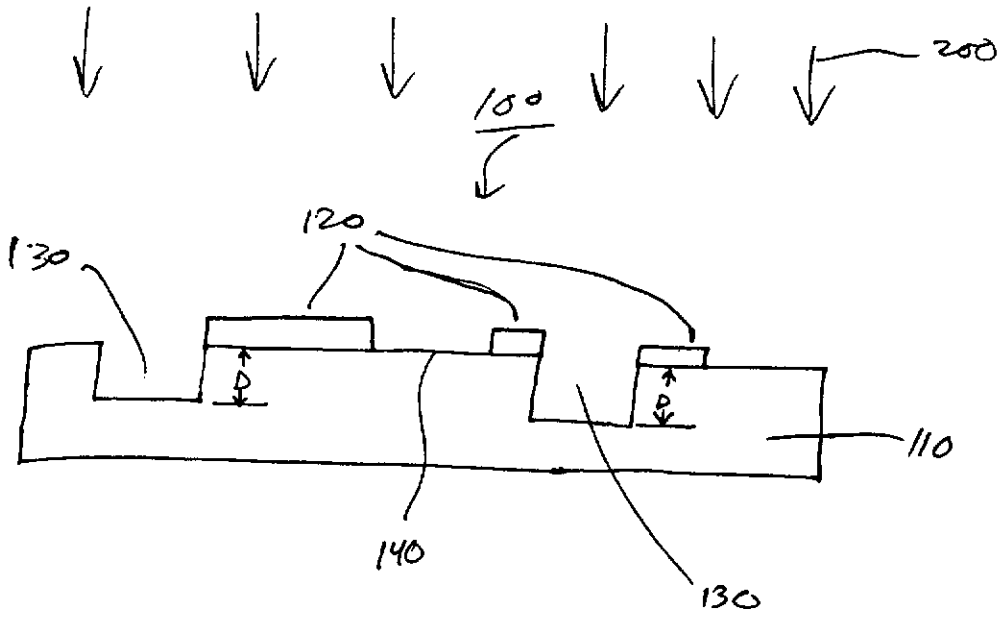


Fig. 2
PRIOR ART

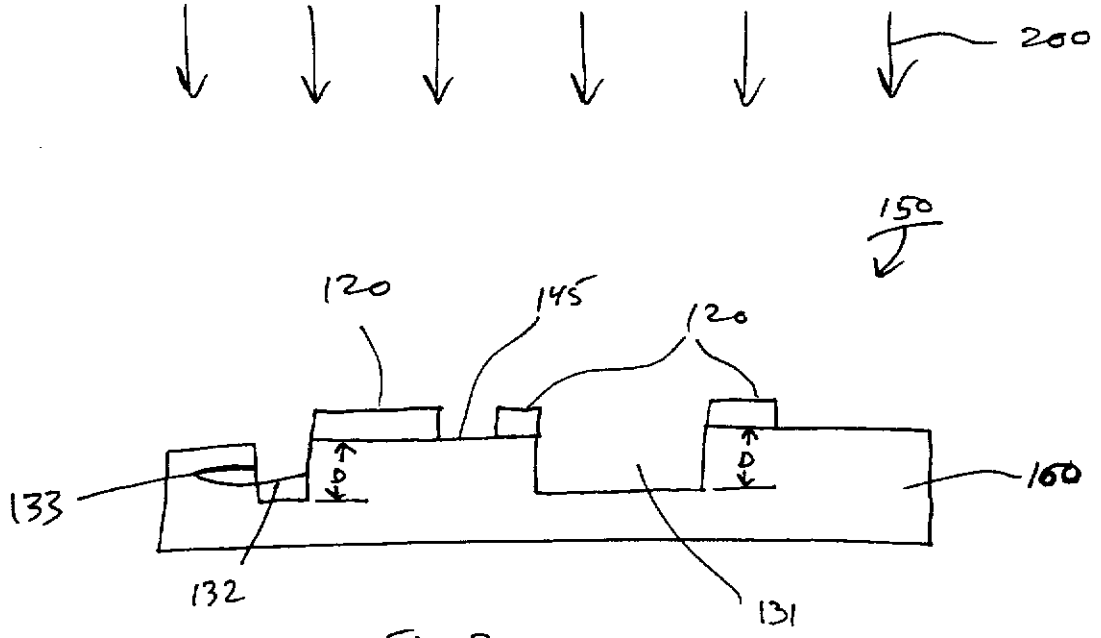


Fig. 3
PRIOR ART

300

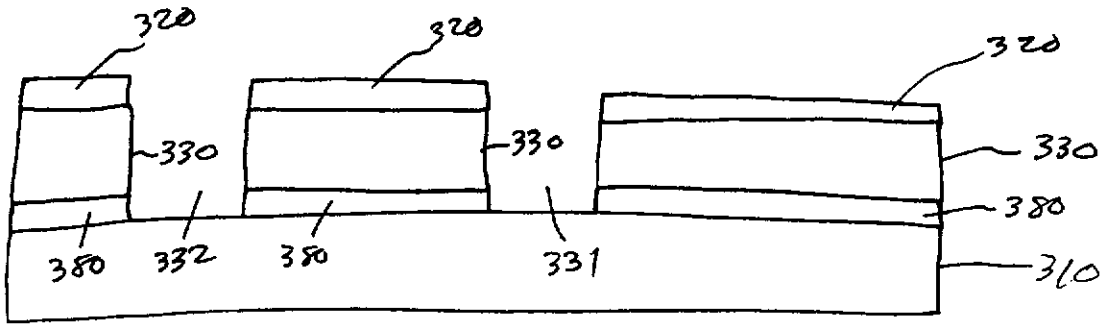


Fig. 4

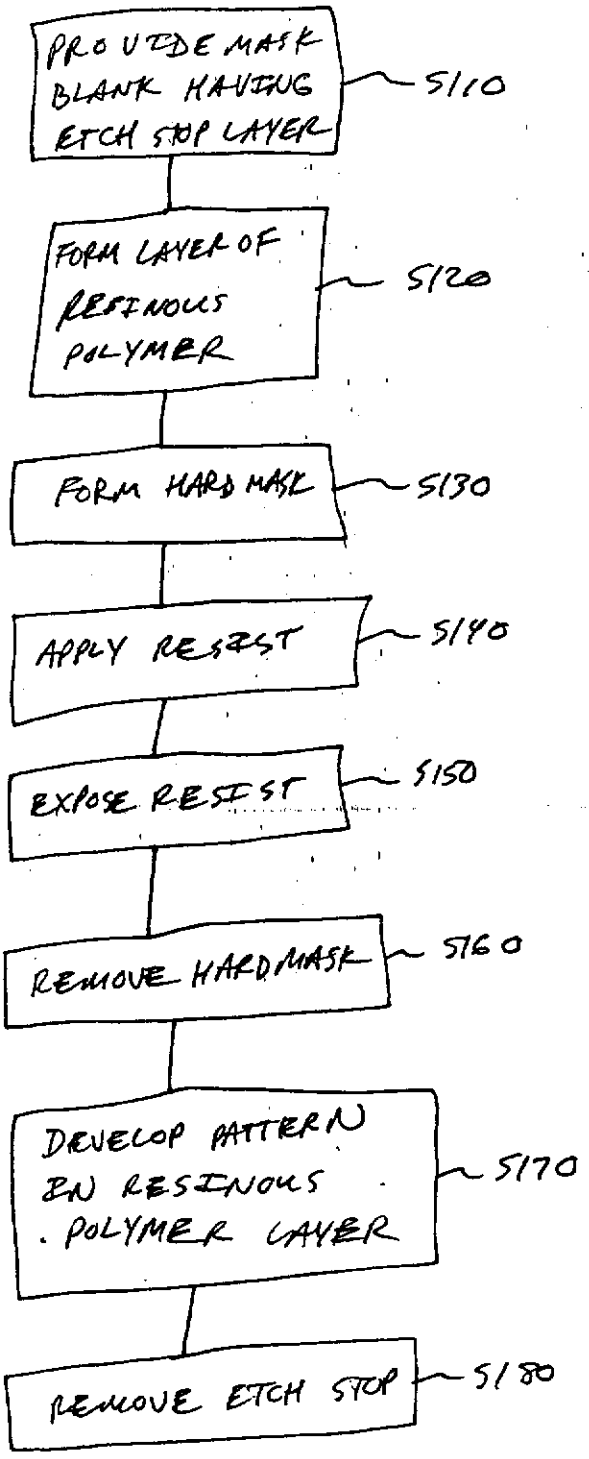

PROVIDE MASK BLANK HAVING ETCH STOP LAYER
S110
FORM LAYER OF RESINOUS POLYMER
S120
FORM HARD MASK
S130
APPLY RESIST
S140
EXPOSE RESIST
S150
REMOVE HARD MASK
S160
DEVELOP PATTERN IN RESINOUS POLYMER LAYER
S170
REMOVE ETCH STOP
S180

Fig. 5

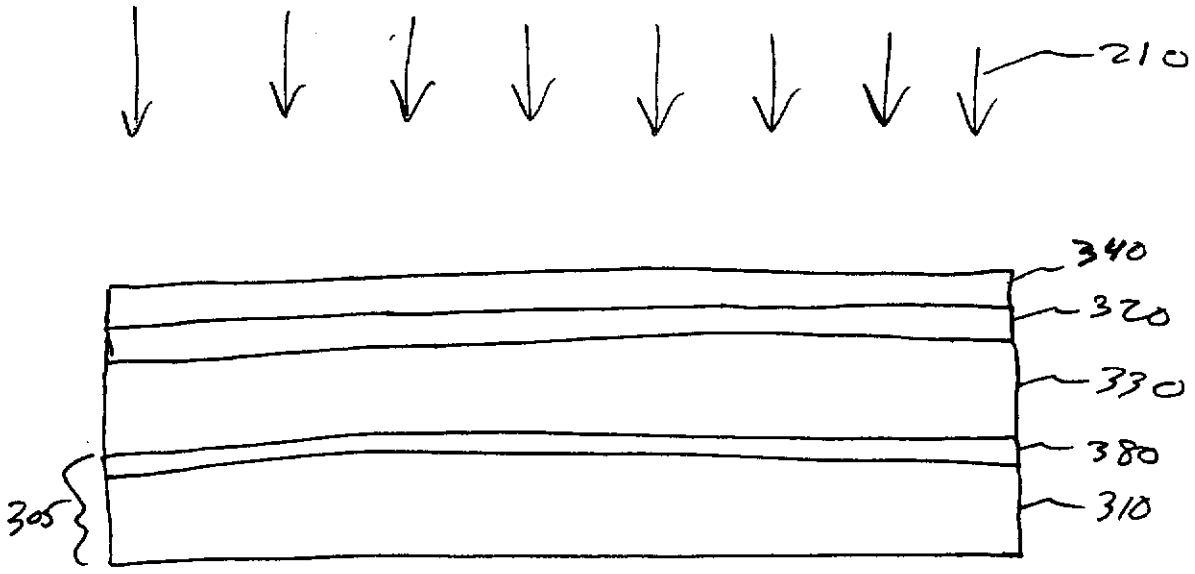

210
340
320
330
380
310
305

Fig. 6

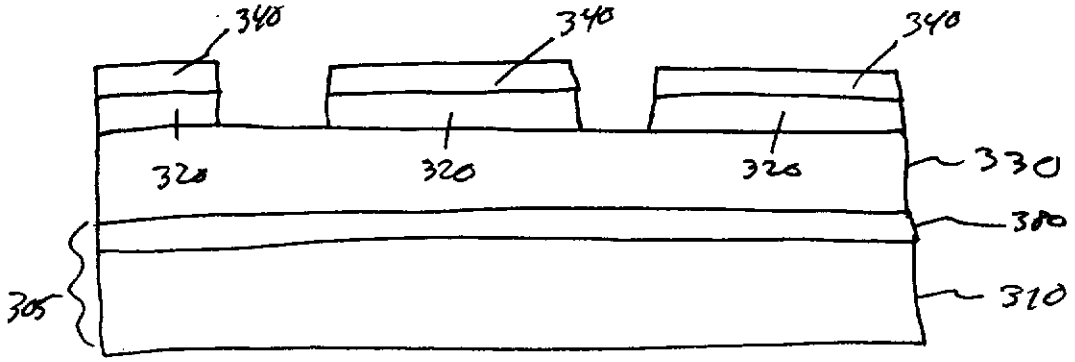

340
340
340
320
320
320
330
380
310
305

Fig. 7

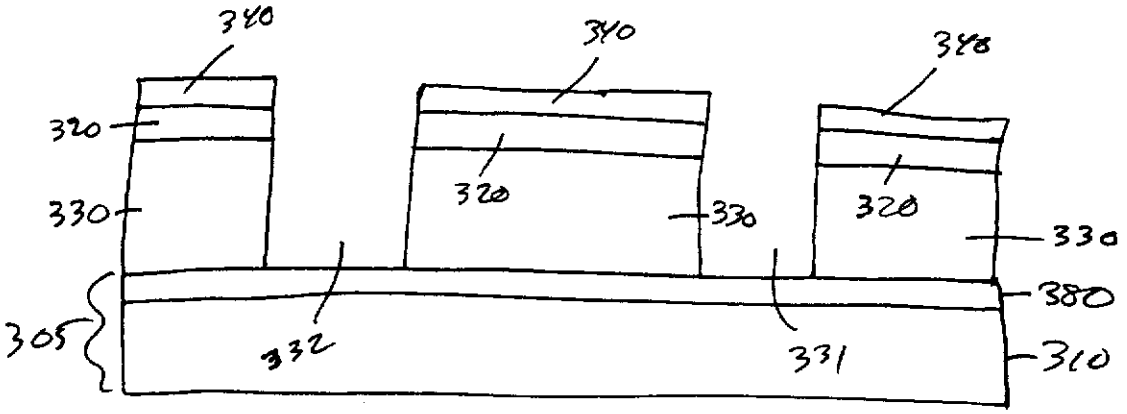

340
340
340
320
320
320
330
330
330
380
305
332
331
310

Fig. 8

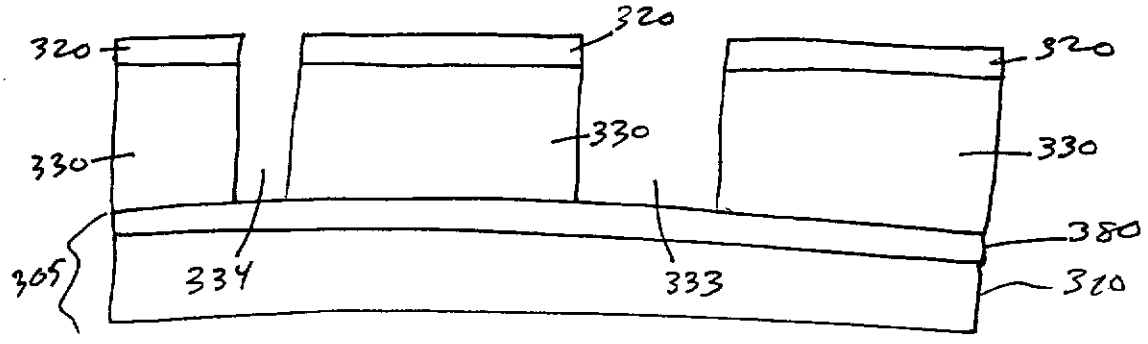

320
320
320
330
330
330
380
305
334
333
310

Fig. 9

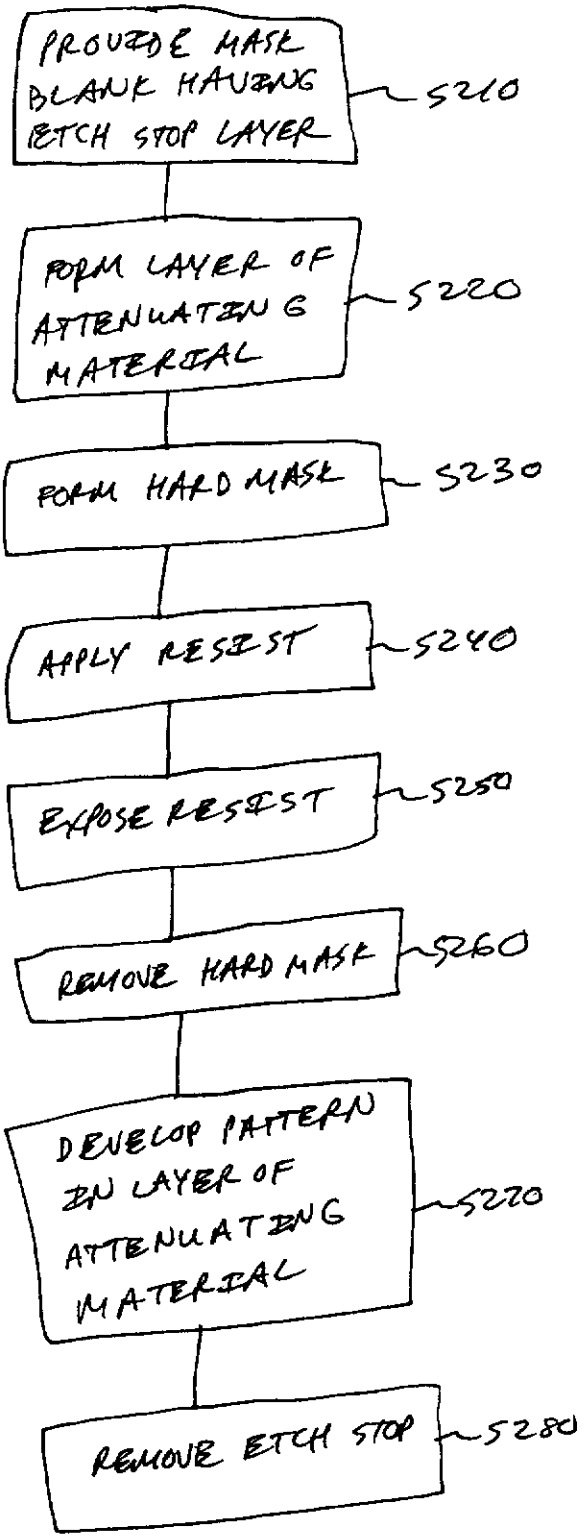

PROVIDE MASK BLANK HAVING ETCH STOP LAYER
S210
FORM LAYER OF ATTENUATING MATERIAL
S220
FORM HARD MASK
S230
APPLY RESIST
S240
EXPOSE RESIST
S250
REMOVE HARD MASK
S260
DEVELOP PATTERN IN LAYER OF ATTENUATING MATERIAL
S270
REMOVE ETCH STOP
S280

Fig. 10

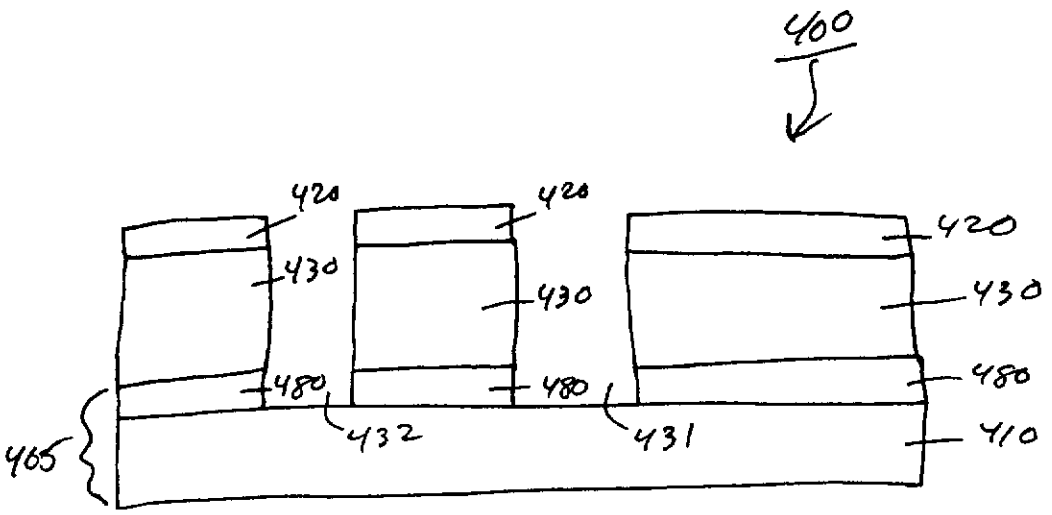


Fig. 11

500

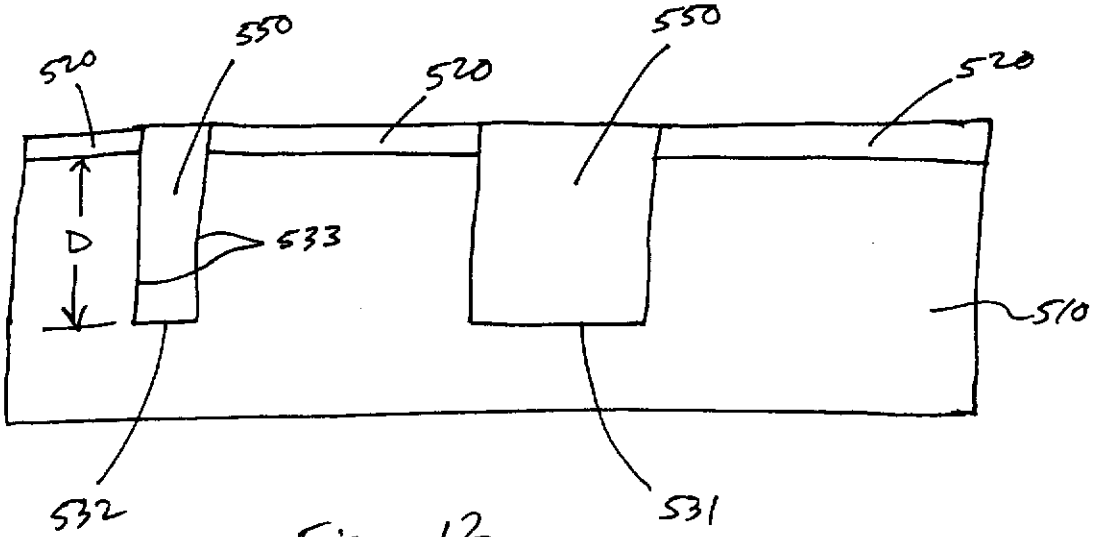


Fig. 12

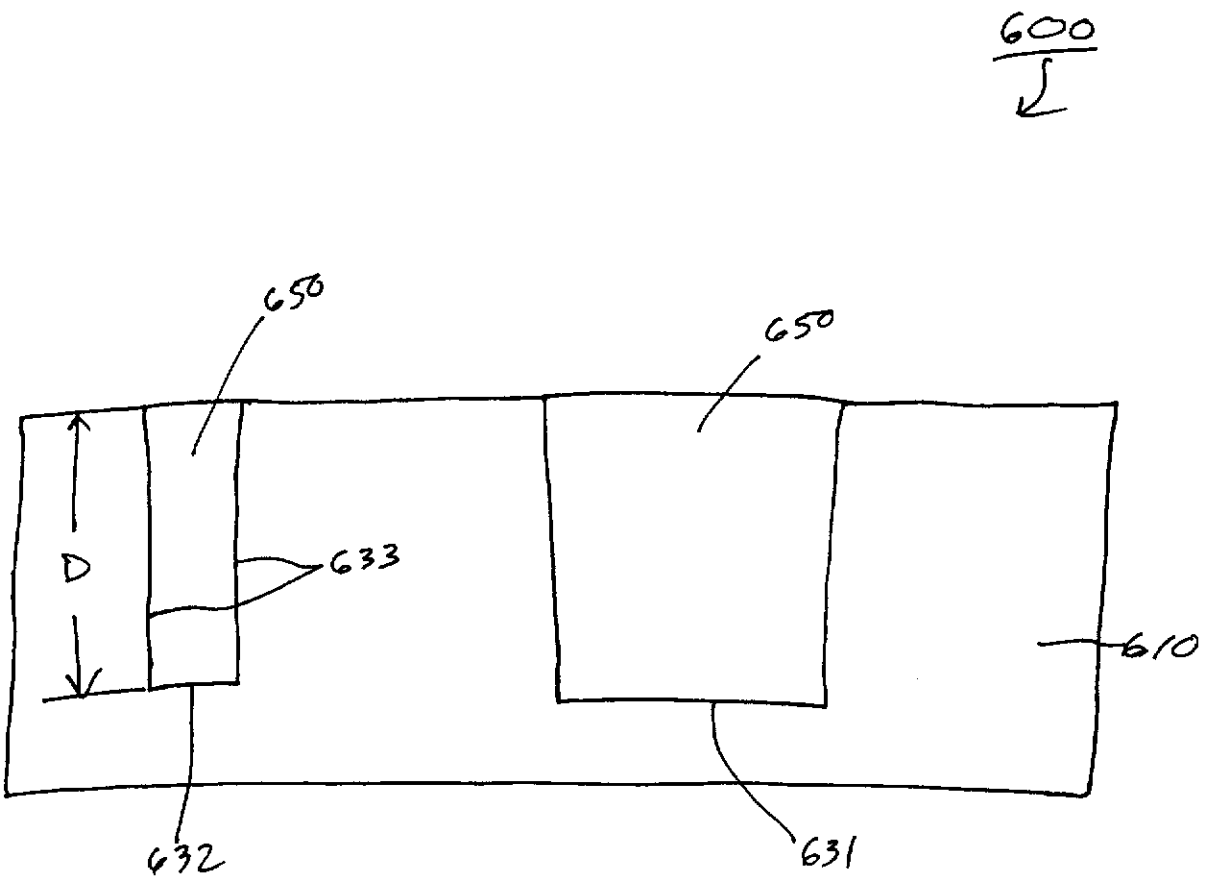


Fig. 13

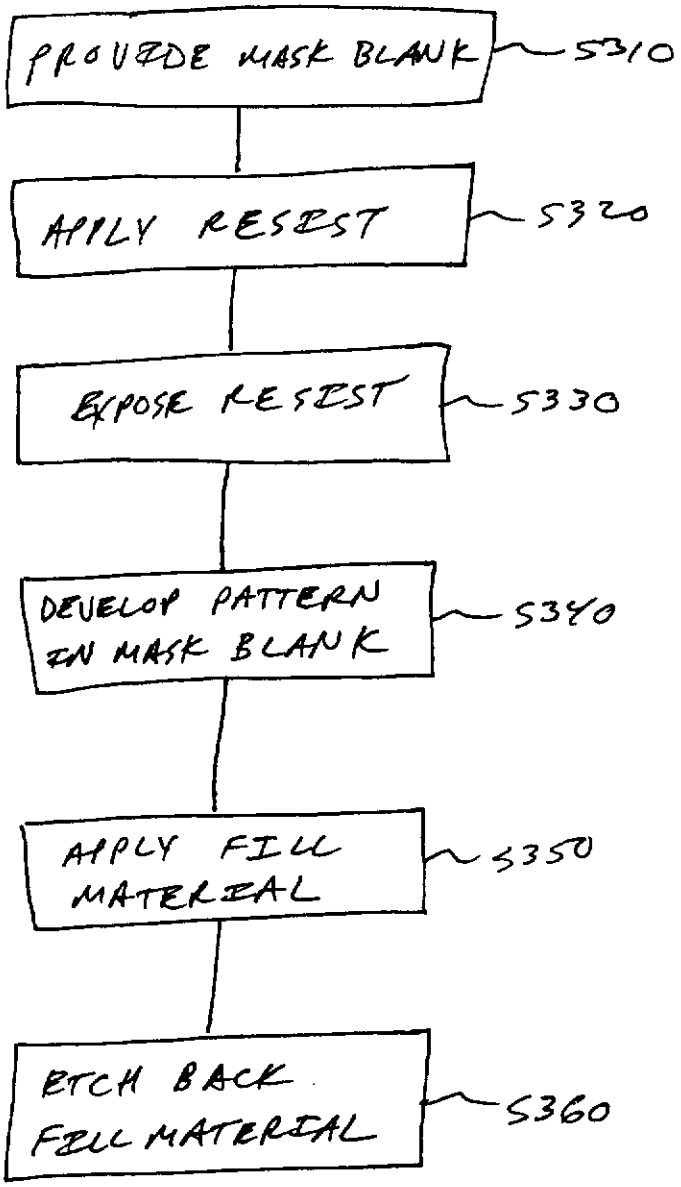

PROVIDE MASK BLANK
S310
APPLY RESIST
S320
EXPOSE RESIST
S330
DEVELOP PATTERN IN MASK BLANK
S340
APPLY FILL MATERIAL
S350
ETCH BACK FILL MATERIAL
S360

Fig. 14

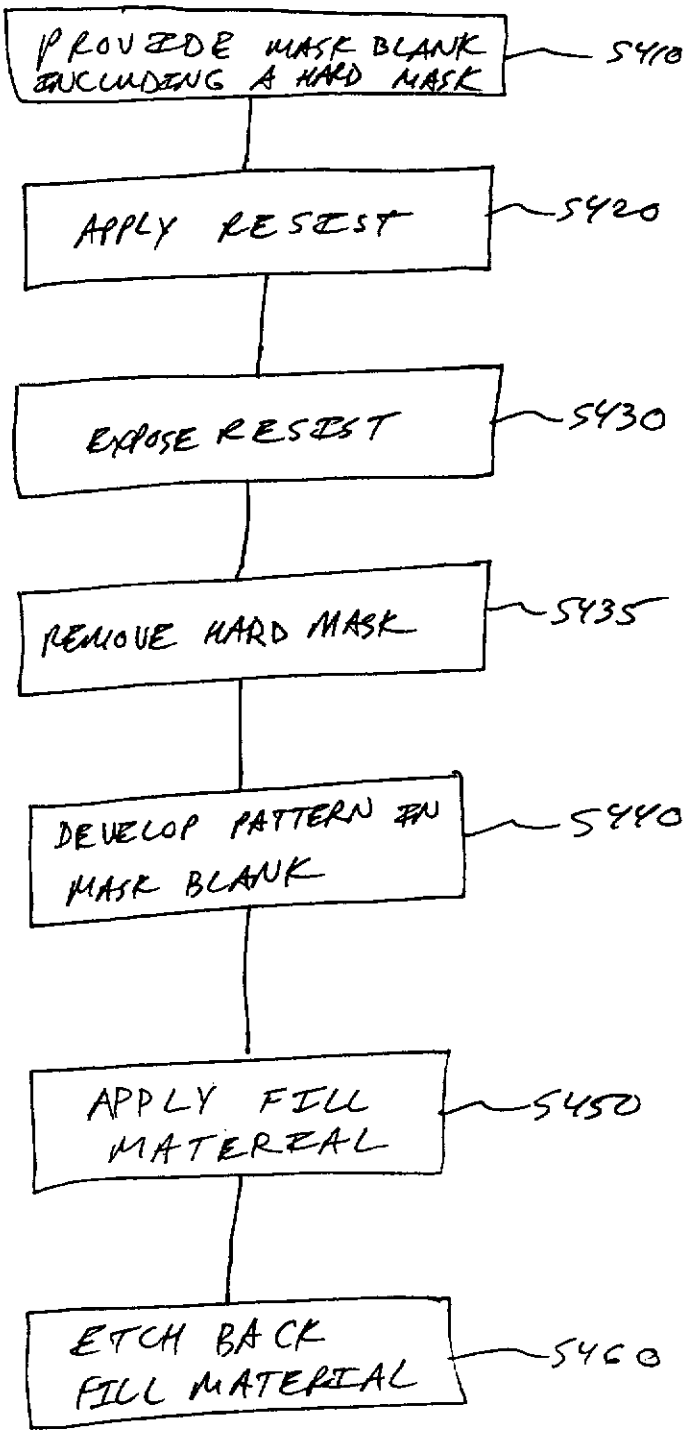

PROVIDE MASK BLANK INCLUDING A HARD MASK
S410
APPLY RESIST
S420
EXPOSE RESIST
S430
REMOVE HARD MASK
S435
DEVELOP PATTERN IN MASK BLANK
S440
APPLY FILL MATERIAL
S450
ETCH BACK FILL MATERIAL
S460

Fig. 15

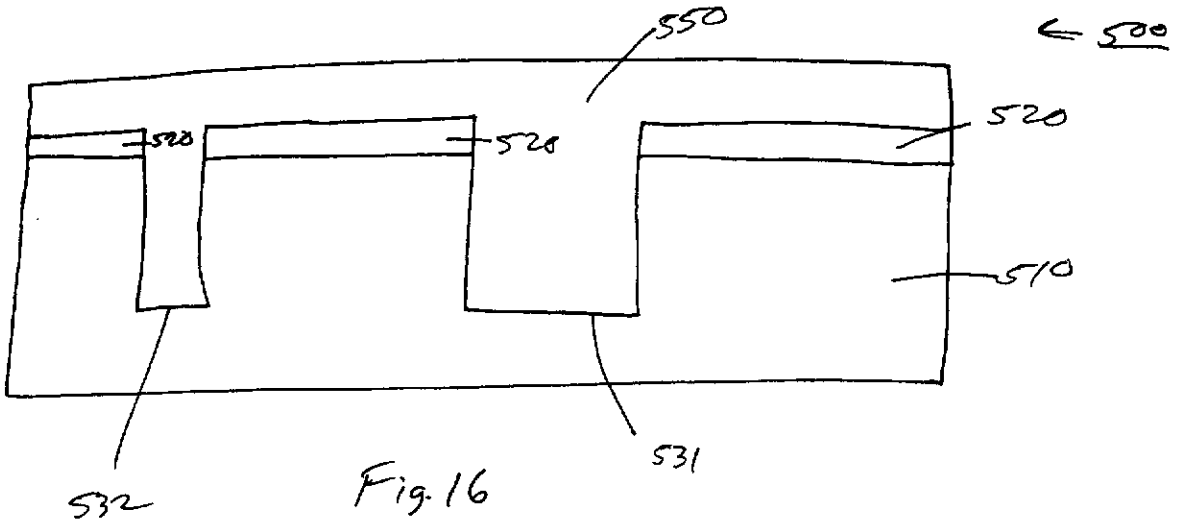


Fig. 16

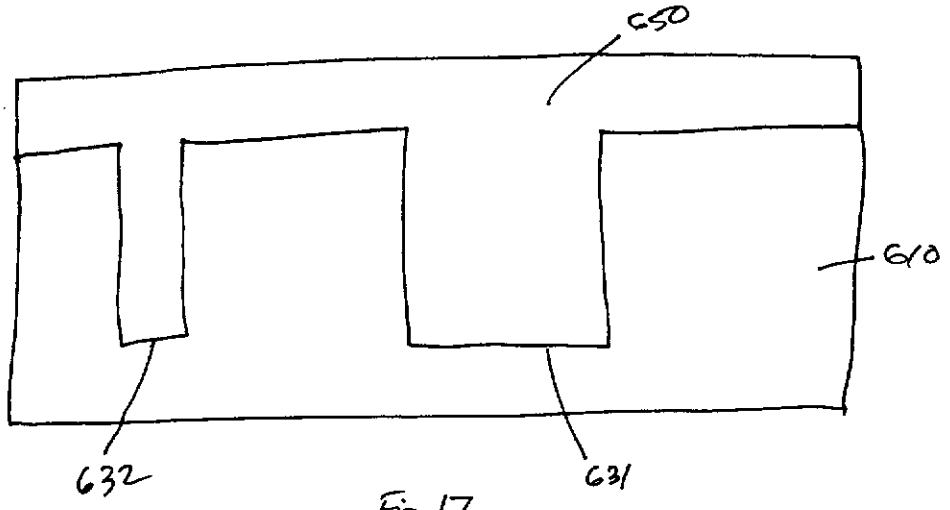


Fig. 17

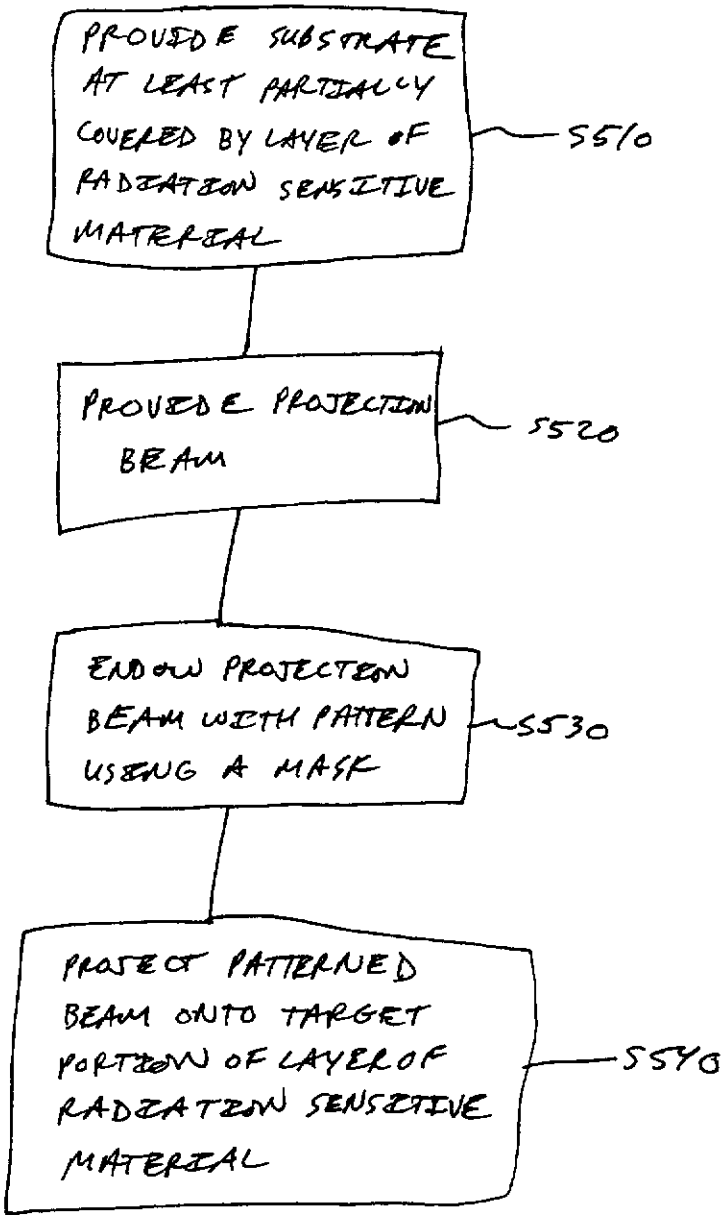

PROVIDE SUBSTRATE AT LEAST PARTIALLY COVERED BY LAYER OF RADIATION SENSITIVE MATERIAL
5510
PROVIDE PROJECTION BEAM
5520
ENDOW PROJECTION BEAM WITH PATTERN USING A MASK
5530
PROJECT PATTERNED BEAM ONTO TARGET PORTION OF LAYER OF RADIATION SENSITIVE MATERIAL
5540

Fig. 18

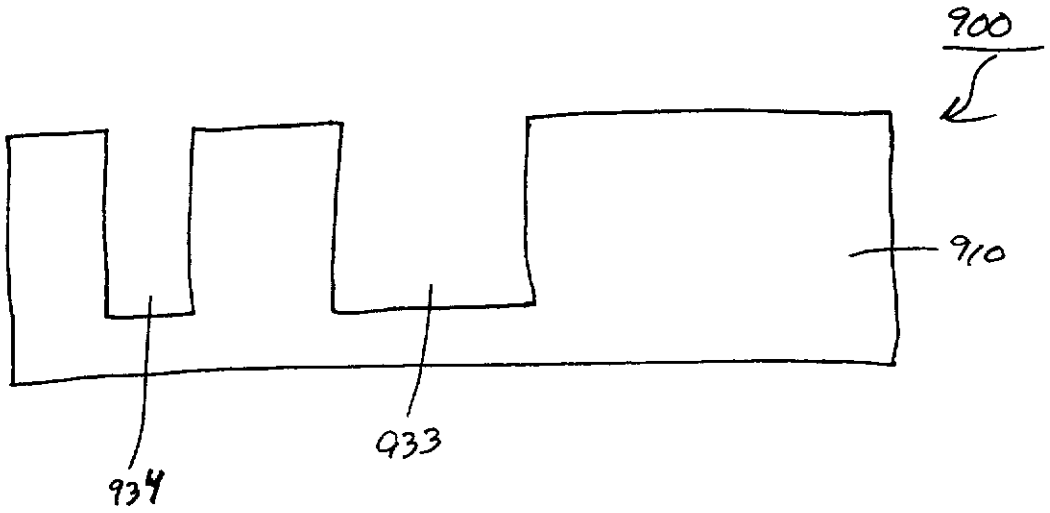


Fig. 19